Low-Voltage CMOS Octal Buffer

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX244 is a high performance, non–inverting octal buffer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows MC74LCX244 inputs to be safely driven from 5 V devices. The MC74LCX244 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable (\overline{OE}) input, when HIGH, disables the output by placing them in a HIGH Z condition.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
 - ♦ Human Body Model >2000 V
 - ♦ Machine Model >200 V
- These Devices are Pb-Free and are RoHS Compliant



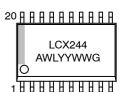
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS

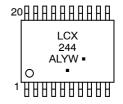


SOIC-20 WB DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 M SUFFIX CASE 967





QFN20 MN SUFFIX CASE 485AA



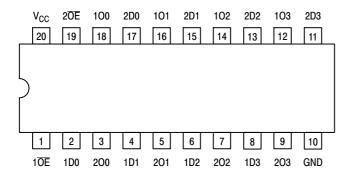
A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.



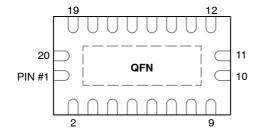


Figure 1. Pinouts: 20-Lead (Top View)

PIN NAMES

PINS	FUNCTION	
nOE	Output Enable Inputs	
1Dn, 2Dn	Data Inputs	
10n, 20n	3-State Outputs	

TRUTH TABLE

INPUTS		OUTPUTS
1 <u>0E</u> 2 <u>0E</u>	1Dn 2Dn	10n, 20n
L	L	L
L	Н	Н
Н	Х	Z

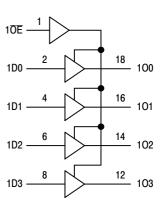
H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State

X = High or Low Voltage Level and Transitions are Acceptable

For I_{CC} reasons, DO NOT FLOAT Inputs



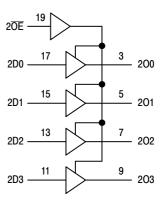


Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Condition	Value	Units
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		$-0.5 \le V_1 \le +7.0$	V
Vo	DC Output Voltage	Output in 3-State	$-0.5 \le V_O \le +7.0$	V
		Output in HIGH or LOW State (Note 1)	$-0.5 \le V_O \le V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current	V _I < GND	-50	mA
I _{OK}	DC Output Diode Current	V _O < GND	-50	mA
		V _O > V _{CC}	+50	mA
Io	DC Output Source/Sink Current		±50	mA
I _{CC}	DC Supply Current Per Supply Pin		±100	mA
I _{GND}	DC Ground Current Per Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
V _O	Output Voltage HIGH or LOW State 3-State	0		V _{CC} 5.5	V
Іон	HIGH Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			-24 -12	mA
I _{OL}	LOW Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			24 12	mA
T _A	Operating Free-Air Temperature	-55		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8 V to 2.0 V, V _{CC} = 3.0 V	0		10	ns/V

^{1.} I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			T _A = −55°C	to +125°C	
Symbol	Characteristic	Condition	Min	Max	Units
V_{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}$	2.0		1
V_{IL}	LOW Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}$		0.8]
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$	V _{CC} - 0.2		V
		$V_{CC} = 2.3 \text{ V}; I_{OH} = -8 \text{ mA}$	1.8		1
		$V_{CC} = 2.7 \text{ V; } I_{OH} = -12 \text{ mA}$	2.2]
		V _{CC} = 3.0 V; I _{OH} = -18 mA	2.4		1
		V _{CC} = 3.0 V; I _{OH} = -24 mA	2.2		1
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6]
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4]
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
II	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5	μА
I _{OZ}	3-State Output Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le V_{O} \le 5.5 \text{ V};$ $V_{I} = V_{IH} \text{ or V }_{IL}$		±5	μА
I _{OFF}	Power-Off Leakage Current	$V_{CC} = 0 \text{ V}; \text{ V}_{I} \text{ or } \text{V}_{O} = 5.5 \text{ V}$		10	μА
I _{CC}	Quiescent Supply Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μА
		$2.3 \le V_{CC} \le 3.6 \text{ V}; 3.6 \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$		±10	
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μА

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS (t_R = t_F = 2.5 ns; R_L = 500 $\Omega)$

					Lin	nits			
					T _A = -55°C	to +125°C			1
			V _{CC} = 3.0	V to 3.6 V	V _{CC} =	2.7 V	V _{CC} = 2.	5 V ± 0.2	7
			C _L =	50 pF	C _L =	50 pF	C _L =	30 pF	7
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Units
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	1.5 1.5	6.5 6.5	1.5 1.5	7.5 7.5	1.5 1.5	7.8 7.8	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	2	1.5 1.5	8.0 8.0	1.5 1.5	9.0 9.0	1.5 1.5	10 10	ns
t _{PHZ} t _{PLZ}	Output Disable Time From High and Low Level	2	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	1.5 1.5	8.4 8.4	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0					ns

^{3.} Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

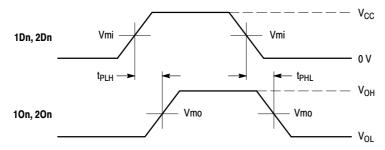
DYNAMIC SWITCHING CHARACTERISTICS

			T	A = +25°C	•	
Symbol	Characteristic	Condition	Min	Тур	Max	Units
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	$\begin{array}{c} V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{array}$		0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	$\begin{array}{c} V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{array}$		-0.8 -0.6		V

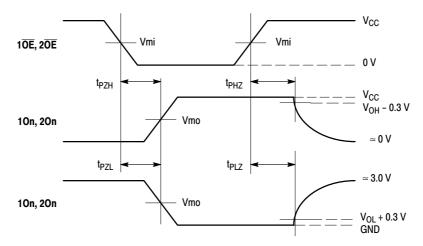
^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF



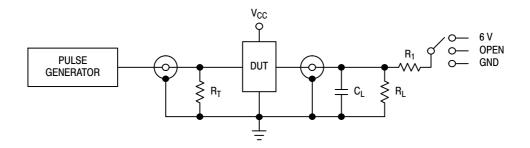
WAVEFORM 1 – PROPAGATION DELAYS $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

Figure 3. AC Waveforms

	V _{CC}			
Symbol	3.3 V \pm 0.3 V	2.7 V	2.5 V \pm 0.2 V	
Vmi	1.5 V	1.5 V	V _{CC} /2	
Vmo	1.5 V	1.5 V	V _{CC} /2	
V_{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V	
V_{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 015 V	



TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V at $V_{CC} = 3.3 \pm 0.3 \text{ V}$ 6 V at $V_{CC} = 2.5 \pm 0.2 \text{ V}$
Open Collector/Drain t _{PLH} and t _{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

 C_L = 50 pF at V_{CC} = 3.3 ± 0.3 V or equivalent (includes jig and probe capacitance) C_L = 30 pF at V_{CC} = 2.5 ± 0.2 V or equivalent (includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

ORDERING INFORMATION

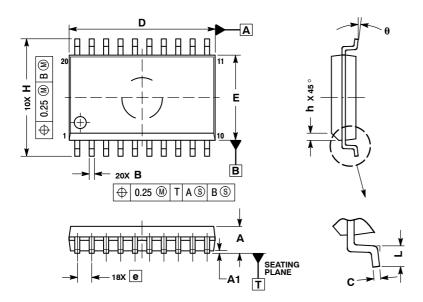
Device	Package	Shipping [†]
MC74LCX244DWG	SOIC-20 WB (Pb-Free)	38 Units / Rail
MC74LCX244DWR2G	SOIC-20 WB (Pb-Free)	1000 / Tape & Reel
MC74LCX244DTG	TSSOP-20*	75 Units / Rail
MC74LCX244DTR2G	TSSOP-20*	2500 / Tape & Reel
MC74LCX244MELG	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel
MC74LCX244MNTWG	QFN20 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

PACKAGE DIMENSIONS

SOIC-20 WB CASE 751D-05 ISSUE G



NOTES:

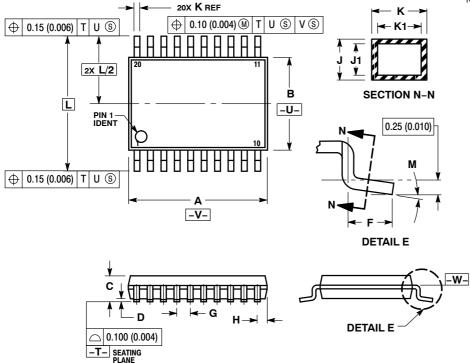
- NOTES:

 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 **ISSUE C**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

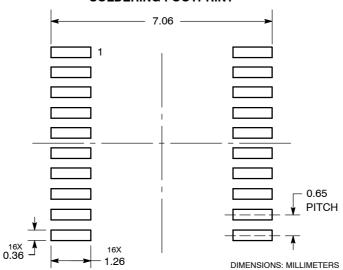
- MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION
 SHALL NOT EXCEED 0.25 (0.01) PER SIDE.
- SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
- CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

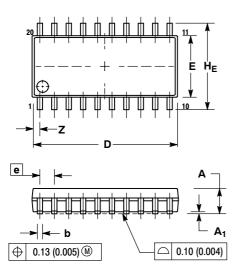
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
_	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8°	0°	8°

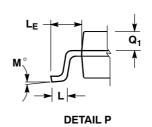
SOLDERING FOOTPRINT

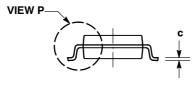


PACKAGE DIMENSIONS

SOEIAJ-20 CASE 967-01 ISSUE A







- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

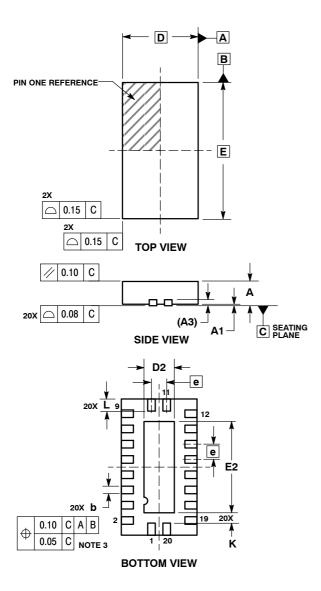
 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003)
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES			
DIM	MIN	MAX	MIN	MAX		
Α		2.05		0.081		
A ₁	0.05	0.20	0.002	0.008		
b	0.35	0.50	0.014	0.020		
C	0.15	0.25	0.006	0.010		
D	12.35	12.80	0.486	0.504		
E	5.10	5.45	0.201	0.215		
е	1.27 BSC		0.050 BSC			
HE	7.40	8.20	0.291	0.323		
L	0.50	0.85	0.020	0.033		
LE	1.10	1.50	0.043	0.059		
M	0 °	10°	0 °	10°		
Q_1	0.70	0.90	0.028	0.035		
Z		0.81		0.032		

PACKAGE DIMENSIONS

QFN20, 2.5x4.5 MM CASE 485AA-01 **ISSUE B**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSIONS b APPLIES TO PLATED
 TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
 COPLANARITY APPLIES TO THE EXPOSED
- PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.80	1.00		
A1	0.00	0.05		
A3	0.20 REF			
b	0.20	0.30		
D	2.50 BSC			
D2	0.85	1.15		
Е	4.50 BSC			
E2	2.85	3.15		
е	0.50 BSC			
K	0.20			
L	0.35	0.45		

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